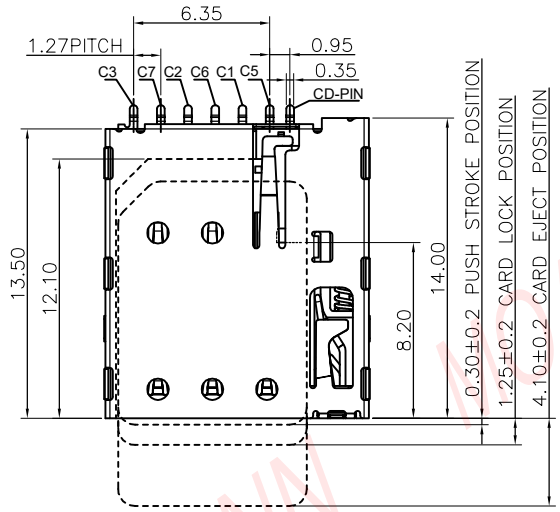
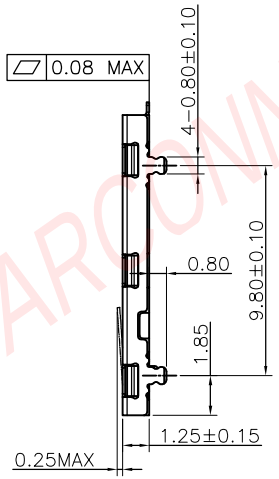
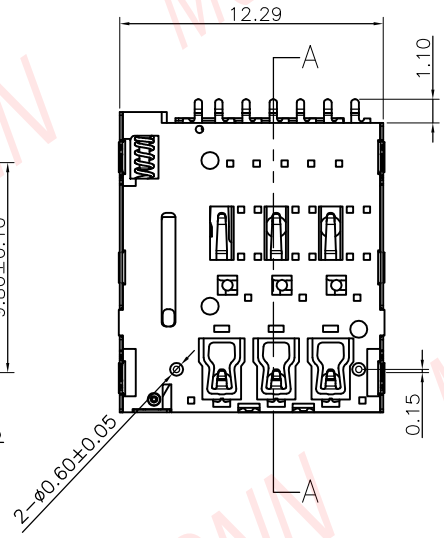
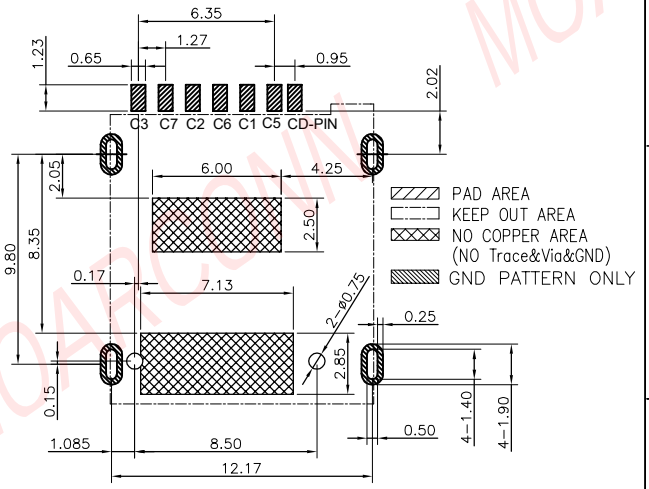
All materials, plating and process meet HF requirements.

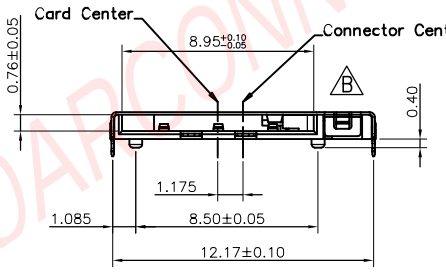


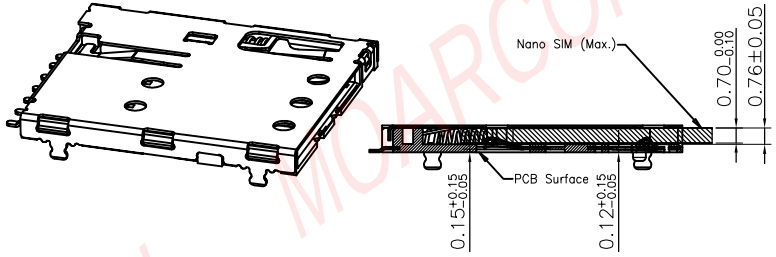






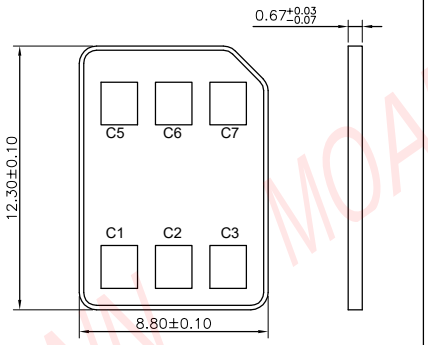
RECOMMEND P.C.B LAYOUT
(General tolerance ±0.05)





Section A–A

NOTE:
1. Material:
   1–1 Housing:High Temperature Thermoplastic,(LCP S475)Color Black UL 94V–0
   1–2 Contact: Phosphor Bronze(C5210R–H,T=0.12±0.01mm)
   1–3 Cover: SUS304–H T=0.12±0.03mm
2. Plating:
   2–1 Contact terminal:
   Contact area: Gold FLASH.
   Solder area: Sn 120u" Min .
   Underplating: Ni overall 50U" Min.
   2–2 Cover:
   Underplating: Ni overall 50U" Min.
3. Specification:
   3–1.Current Rating :0.5A max.
   3–2.Contact Resistance: 50 mOhms max
   3–3.Insulation Resistance:1000 MOhms min./500VDC
   3–4.Dielectric Withstanding Voltage:500 V AC/1minute
   3–5.Operating Temperature:–25°C to+85°C
   3–6.Mating Cycles:5000 Insertions



COMPOSITION OF DETECTION
CARD DETECT(SW)
GND SW
CARD DETECTION/SWITCH
CARD INSTALLATION: OPEN NORMAL: SHORT

SIM Card Pin Assignments

NANO SIM CARD	
C1	Vcc
C2	RST
C3	CLK
C5	GND
CD	CD/SW
C6	Vpp
C7	I/O

REVISION NO.	ECR NO.	DESCRIPTION	MARK	DATE
B	ER2109140	Add the latch	FAJI	2021.07.28

DIMENSIONS INIT: mm
UNLESS OTHERWISE SPECIFIABLE

DIMENSION	TOLERANCE
X.X: ±	0.35
X.XX: ±	0.20
X.XXX: ±	0.10
ANGULAR: ±	2°

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DONG GUAN MOARCONN ELECTRONIC Co., Ltd.

PRODUCT NAME : NANO SIM H1.25 PUSH/PUSH	DRAWING: FAJI	DATE: 2021.07.28
PRODUCT NO. : NS125–T1250–02	CHECK:	DATE:
DRAWING NO. : D–NS125–T1250–02	APPROVED:	DATE:

SCALE:	DWG ID:	REV.:	PAGE:
1:1	C D	B	1 OF 1

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